

isc N-Channel MOSFET Transistor IPD60R460CE,IIPD60R460CE

• FEATURES

- Static drain-source on-resistance:
 $R_{DS(on)} \leq 0.46 \Omega$
- Enhancement mode:
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

• DESCRIPTION

- Fast switching

• ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

| SYMBOL | PARAMETER | VALUE | UNIT |
|------------------|---|---------|------|
| V _{DSS} | Drain-Source Voltage | 600 | V |
| V _{GS} | Gate-Source Voltage | ±20 | V |
| I _D | Drain Current-Continuous | 13.1 | A |
| I _{DM} | Drain Current-Single Pulsed | 26 | A |
| P _D | Total Dissipation @T _c =25°C | 102 | W |
| T _j | Max. Operating Junction Temperature | 150 | °C |
| T _{stg} | Storage Temperature | -40~150 | °C |

• THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | MAX | UNIT |
|----------------------|---------------------------------------|------|------|
| R _{th(j-c)} | Channel-to-case thermal resistance | 1.22 | °C/W |
| R _{th(j-a)} | Channel-to-ambient thermal resistance | 62 | °C/W |



| DIM | mm | |
|-----|------|------|
| | MIN | MAX |
| A | 6.40 | 6.60 |
| B | 5.20 | 5.40 |
| C | 1.15 | 1.35 |
| D | 5.70 | 6.10 |
| F | 0.65 | |
| G | 0.75 | |
| H | 2.10 | 2.50 |
| J | 2.10 | 2.40 |
| K | 0.40 | 0.60 |
| L | 0.90 | 1.10 |
| Q | 9.90 | 10.1 |

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ELECTRICAL CHARACTERISTICS

T_C=25°C unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP | MAX | UNIT |
|---------------------|--------------------------------|---|-----|-----|------|------|
| BV _{DSS} | Drain-Source Breakdown Voltage | V _{GS} =0V; I _D =0.25mA | 600 | | | V |
| V _{GS(th)} | Gate Threshold Voltage | V _{DS} =V _{GS} ; I _D =0.28mA | 2.5 | | 3.5 | V |
| R _{DS(on)} | Drain-Source On-Resistance | V _{GS} =10V; I _D =3.4A | | | 0.46 | Ω |
| I _{GSS} | Gate-Source Leakage Current | V _{GS} =20V; V _{DS} =0V | | | 0.1 | μA |
| I _{DSS} | Drain-Source Leakage Current | V _{DS} =600V; V _{GS} = 0V | | | 1 | μA |
| V _{SD} | Diode forward voltage | I _F =4.2A, V _{GS} = 0V | | 0.9 | | V |